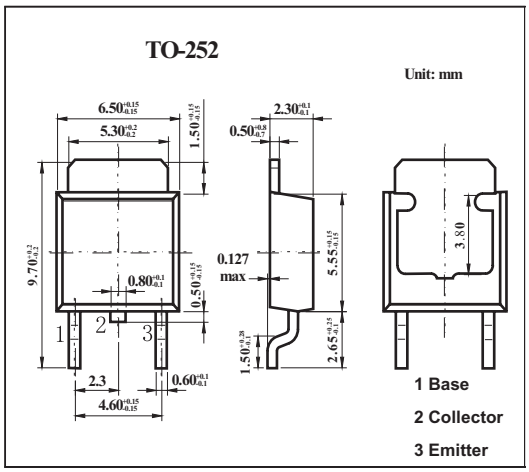
Silicon PNP Epitaxial Planar Type

2SB967



■ Features

- Possible to solder the radiation fin directly to printed cicuit board.
- Low collector-emitter saturation voltage $V_{CE(sat)}$.
- Large collector current I_C.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-27	V
Collector-emitter voltage	V_{CEO}	-18	V
Emitter-base voltage	V_{EBO}	-7	V
Collector current	I_C	-5	A
Peak collector current	I_{CP}	-8	A
Collector power dissipation	P_C	20	W
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base cutoff curent	I_{CBO}	V_{CB} = -10 V,I_E = 0			-100	nA
Emitter-base cutoff current	I_{EBO}	V_{EB} = -5 V, I_C = 0			-1	μA
Collector-emitter voltage	V_{CEO}	I_C = -1mA, I_B = 0	-18			V
Emitter-base voltage	V_{EBO}	I_E = -10 μA, I_C = 0	-7			V
Forward current transfer ratio	h_{FE}	V_{CE} = -2 V, I_C = 2 A	90		625	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = -3 A, I_B = -0.1 A			-1	V
Transition frequency	f_T	V_{CE} = -6 V, I_E = -50 mA , f = 200 MHz		120		MHz
Collector output capacitance	C_{ob}	V_{CB} = -20V , I_E = 0 , f = 1.0MHz			85	pF

■ h_{FE} Classification

Rank	P	Q	R
h_{FE}	90～135	125～205	180～625